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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No.:	10/821,751	)	Group Art Unit:	2891
Filing Date:	December 30, 2002	)	Examiner:	Yevsikov, Victor V.
For:	Surface Treatment Using Iodine Plasma To Improve Metal Deposition	)	Docket No:	101.114
Inventors:	Dalton et al.	)	Confirmation No.:	1874
		)	Paper No.:	

MAIL STOP AMENDMENT  
COMMISSIONER FOR PATENTS  
P.O. BOX 1450  
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Sir:

This Amendment and Remarks is in response to the Office Action mailed June 15, 2005. In accordance with 37 CFR 1.132, a Declaration Of Sanjay Gopinath is attached.

**AMENDMENTS TO SPECIFICATION**

Please delete and replace a paragraph, as follows.

Please delete the paragraph in the specification at page 3, lines 1—18:

**Deleted paragraph:**

Pretreating a substrate surface with iodine has been reported to increase the growth rate of copper deposited by a MOCVD technique using Cu(hfac)TMVS precursor. United States Patent No. 6,413,864 issued July 2, 2002 to Pyo et al., discloses forming a chemical enhancement layer (CE layer) on a nitride barrier layer surface (e.g., TiN, TaN, WN) with an iodine-containing liquid compound prior to forming a copper seed layer by MOCVD, and then electroplating a second copper layer onto the seed layer. United States Patent No.

**Serial No. 10/821,751**  
**Amendment And Remarks In Response To**  
**Office Action Mailed 06/15/05**

**Page 1**  
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